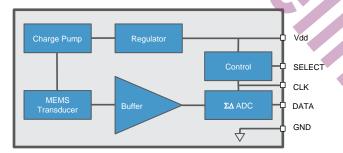
# MULTIMODE DIGITAL VIBRATION SENSOR



The V2S200D is a miniature, high-performance, low power, digital Voice Vibration Sensor (V2S) with a single bit PDM output. Derived from Knowles proven high performance SiSonic™ MEMS technology, the V2S200D consists of a transducer, a low-noise input buffer, and a sigma-delta modulator. These devices provide high vibration sensitivity suitable for picking up audio via bone conduction in devices such as earphones, wearables, and other applications where flat response to vibration and excellent acoustic isolation are required. In addition, the V2S200D offers multiple clock modes for wide compatibility with audio codecs.

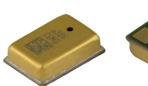


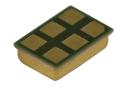
## ABSOLUTE MAXIMUM RATINGS

Table 1: Absolute Maximum Ratings

Parameter	Absolute Maximum Rating	Units
Vdd to Ground	-0.5, +5.0	V
DATA, CLOCK, SELECT to Ground	-0.3, +5.0	V
Input Current	±5	mA
Short Circuit to/from DATA	Indefinite to Ground or Vdd	sec
Storage Temperature	-40 to +100	°C
Operating Temperature	-40 to +85	°C

Stresses exceeding these "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation at these or any other conditions beyond those indicated under "Performacne & Electrical Specifications" is not implied. Exposure beyond those indicated under "Performance & Electrical Specifications" for extended periods may affect device reliability.





## PRODUCT FEATURES

- Low Current Consumption in Low-Power Mode
- Wide Sensor Bandwidth (4kHz)
- High Drive Capability
- Supports Dual Multiplexed Channels
- Multiple Performance Modes (Sleep, Low-Power, Normal)
- Ultra-Stable Performance
- Standard SMD Reflow
- LGA Package

## TYPICAL APPLICATIONS

- Earphones
- Wearables
- Wind Noise Reduction
- Self Speech Detection
- Imposter Rejection





# PERFORMANCE & ELECTRICAL SPECIFICATIONS<sup>1</sup>

## Table 2: General Sensor Specifications

Test Conditions: 23  $\pm$ 2°C, 55 $\pm$ 20% R.H., Vdd=1.8 V, Tedge  $\leq$  3ns, unless otherwise indicated

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Supply Voltage	Vdd		1.65	1.8	3.3	V
Bandwidth	BW	±3dB relative to 1 kHz	-	4	-	kHz
Resonant Frequency Peak	Fres	Acceleration response	-	7	-	kHz
Council colotion		1 g sinewaye output / 94dB SPL @ 100 Hz	-	50	-	-ID
Sound Isolation		1 g sinewave output / 94dB SPL @ 1kHz	-	50	-	- dB
DC Offset		Fullscale = ±100 (SEL=Low / SEL=High)	-	0.0 / 0.78	-	% FS
Polarity		+Z axis (Refer to Mechanical Specs for axis definition)	Increasing	density of 1's	3	
Data Format			½ Cycle PI	OM		
Sensitivity Drop		Vdd(min) ≤ Vdd ≤ Vdd(max)	-	-	±TBD	dB
Clock Input Capacitance	Cin		-	5	-	pF
Data Output Capacitance	Cout		-	5	-	pF
Data Output Load	Cload		-	-	160	pF
SELECT (high)			Vdd-0.2	-	3.3	V
SELECT (low)			-0.3	-	0.2	V
Short Circuit Current	Isc	Grounded DATA pin	1	-	20	mA
Startup Time <sup>3</sup>		Powered Down → Active, S within 1 dB of final value	-	-	20	ms
Time to First Data Bit <sup>4</sup>		Time from valid Vdd and CLK until the first logical bit is driven on the DATA line. The output is tristate until First Data Bit.	-	5	-	ms
Mode-Change Time <sup>3, 4</sup>		Low Power Mode ⇔ Normal Mode, S within 1 dB of final value		-	20	ms





Table 3: Normal Mode

 $Test\ Conditions: 23\ \pm 2^{\circ}C, 55\pm 20\%\ R.H.,\ Vdd=1.8\ V,\ Fclock=2.4\ MHz\ (D.C.=50\%),\ Tedge\leq 3ns,\ SELECT\ grounded,\ no\ load,\ unless\ otherwise\ indicated$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Units
		Fclock = 1.2 MHz	-	480	-	
		Fclock = 1.536 MHz	-	550	-	
Supply Current <sup>2</sup>	Idd	Fclock = 2.4 MHz	-	700	-	μΑ
		Fclock = 3.072 MHz	-	850	-	
Sensitivity	S	1g @ 1 kHz (Z-Axis)	-26	-25	-24	dBFS/g
		1 g @ 1 kHz, A-weighted (BW = 100 - 4kHz), Fclock = 1.2 MHz	-	63.5	-	
		1 g @ 1 kHz, A-weighted (BW = 100 - 4kHz), Fclock = 1.536 MHz	_	63.5	_	
Signal To Noise Ratio	SNR	1 g @ 1 kHz, A-weighted (BW = 100 - 4kHz), Fclock = 2.4 MHz	-	64.5	-	dB(A)
		1 g @ 1 kHz, A-weighted (BW = 100 - 4kHz), Fclock = 3.072 MHz	-	64.5	-	
Noise Density		@1kHz	-	9	-	μg/√Hz
Total Harmonic Distortion	THD	1g @ 1 kHz	-	0.25	-	%
Total Harmonic Distortion		1% THD @ 1 kHz, S = typ	-	>10	-	g
Acoustic Overload Point	AOP	10% THD @ 1 kHz, S = typ	-	>10	-	g
Power Supply Rejection Ratio	PSRR	200 mVpp sinewave @ 1 kHz	-	85	-	dB V/FS
Power Supply Rejection	PSR+N	200 mVpp 7/8 duty cycle rectangular waveform @ 217 Hz, A-weighted	-	-80	-	dBFS(A)

## Table 4: Low-Power Mode

Test Conditions: 23  $\pm$ 2°C, 55 $\pm$ 20% R.H., Vdd=1.8 V, Fclock = 800 kHz (D.C. = 50%), Tedge  $\leq$  3ns, SELECT grounded, no load, unless otherwise indicated

Parameter	Symbol	Conditions		Min	Тур	Max	Units
Supply Current <sup>2</sup>	Idd		/	-	290	-	μΑ
Sensitivity	S	1g @ 1 kHz (Z-Axis)		-26.5	-25.5	-24.5	dBFS/g
Signal To Noise Ratio	SNR	1g @ 1 kHz, A-weighted (BW = 100 - 4 kHz)		-	63	-	dB(A)
Noise Density		@1kHz		-	11	-	$\mu g/\sqrt{Hz}$
Total Harmonic Distortion	THD	1g @ 1 kHz		-	0.25	-	%
Total Harmonic Distortion		1% THD @ 1 kHz, S = typ		-	>10	-	g
Acoustic Overload Point	AOP	10% THD @ 1 kHz, S = typ		-7	>10	-	g
Power Supply Rejection Ratio	PSRR	200 mVpp sinewave @ 1 kHz		-	80	_	dBV/FS





Parameter	Symbol	Conditions	Min	Тур	Max	Units
Power Supply Rejection	PSR+N	200 mVpp 7/8 duty cycle rectangular waveform @ 217 Hz, A-weighted	-	-80	-	dBFS(A)

#### Table 5: Sleep Mode

Test Conditions: 23 ±2°C, 55±20% R.H., Vdd=1.8 V, Fclock grounded, SELECT grounded, no load, unless otherwise indicated

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Sleep Current	Isleep	CLOCK = Pulled Low, DATA = High-Z	-	0.5	10	μΑ

<sup>&</sup>lt;sup>1</sup> Sensitivity and Supply Current are 100% tested.

#### Table 6: Digital Interface

Test Conditions: 23 ±2°C, 55±20% R.H., Vdd=1.8 V, Tedge ≤ 3ns, unless otherwise indicated

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Logic Input High <sup>5</sup>	Vih		0.7xVdd	-	3.3	V
Logic Input Low <sup>5</sup>	Vil		-0.3	-	0.3xVdd	V
Logic Output High <sup>5</sup>	Voh	I <sub>OUT</sub> = 2 mA	Vdd-0.45	-	Vdd	V
Logic Output Low <sup>5</sup>	Vol	I <sub>OUT</sub> = 2 mA	0	-	0.45	V
Low→High Threshold <sup>6</sup>	VI-h		-	-	0.7xVdd	V
High→Low Threshold <sup>6</sup>	Vh-l		0.3xVdd	-	-	V
Hysteresis Width <sup>6</sup>	Vhyst	4/	0.10xVdd	-	0.29xVdd	V
		Sleep Mode	-	-	0	1.11-
Clock Frequency <sup>5</sup>	Fclock	Low-Power Mode	600	-	950	kHz
		Normal Mode	1.2	-	3.3	MHz
Clock Duty Cycle	D.C.		40	50	60	%
Delay Time to Data Line Driven <sup>5</sup>	Tdd		18	-	40	ns
Delay Time to Valid Data <sup>5</sup>	Tdv	Max Cload	-	-	100	ns
Delay Time to High Z <sup>5</sup>	Tdz		5	-	16	ns
Hold Time <sup>5</sup>	Thold	Thold, as observed by the input device, will be dependent on Cload	5	-	_	ns

 $<sup>^{5}</sup>$  See Figure 1: Timing Diagram.



<sup>&</sup>lt;sup>2</sup> Idd varies with Cload according to:  $\Delta$ Idd = 0.5\*Vdd\* $\Delta$ Cload\*Fclock.

<sup>&</sup>lt;sup>3</sup> Valid sensor states are: Powered Down Mode (mic off), Sleep Mode (low current, DATA = high-Z, fast startup), Low-Power Mode (low clock speed) and Normal Mode.

<sup>&</sup>lt;sup>4</sup> Output is temporarily muted during the transition between any sensor state.

<sup>&</sup>lt;sup>6</sup> See Figure 2: Hysteresis Diagram.



Figure 1: Timing Diagram

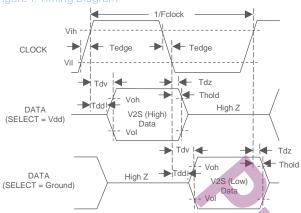


Figure 2: Hysteresis Diagram

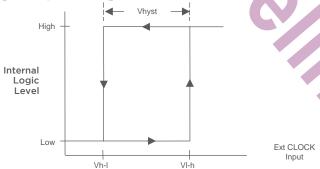


Figure 3: State Diagram

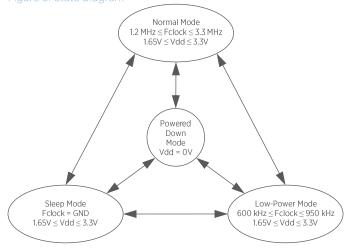


Figure 4: Typical Stereo Application Circuit

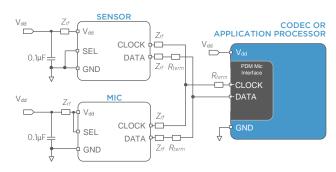
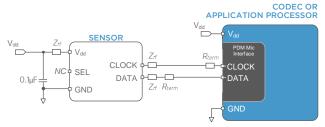


Figure 5: Typical Single-Sensor Application Circui



#### **NOTES**

All Ground pins must be connected to ground.

If necessary to improve RF performance, optional series components (resistors, ferrites, etc.) should be placed closest to the sensor pads.

Bypass capacitors should be placed near each Vdd pin for best performance. Capacitors near the sensor should not contain Class 2 dielectrics due to their piezoelectric effect.

Table 7: SELECT Functionality

Sensor	SELECT	Asserts DATA on	Latch DATA on
V2S (High)	Vdd	CLK rising edge	CLK falling edge
V2S (Low)	Ground	CLK falling edge	CLK rising edge





# PERFORMANCE CURVES

Test Conditions: 23 ±2°C, 55±20% R.H., Vdd=1.8 V, Fclock = 2.4 MHz, SELECT grounded, no load, unless otherwise indicated

Figure 6: Typical Acceleration Magnitude

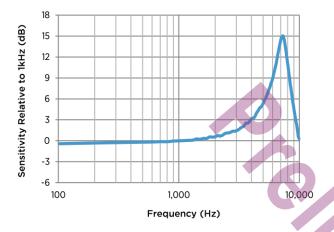


Figure 7: Typical Phase and Group Delay

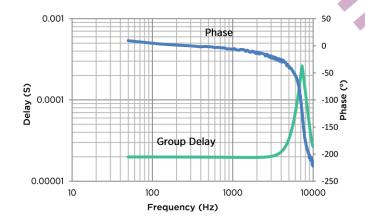


Figure 8: Typical THD vs Acceleration

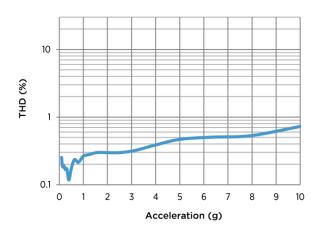


Figure 9: Typical THD vs Frequency

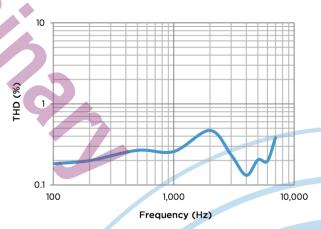




Figure 10: Typical Idd vs Vdd

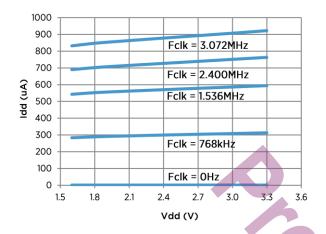


Figure 11: Noise Floor Amplitude Spectral Density

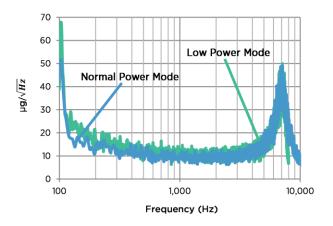
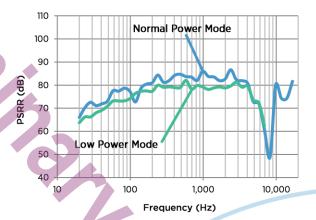


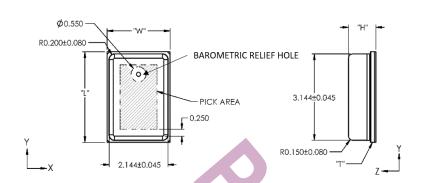
Figure 12: Typical PSRF

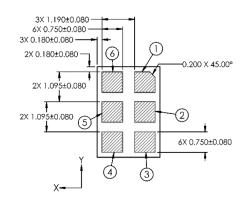






# **MECHANICAL SPECIFICATIONS**

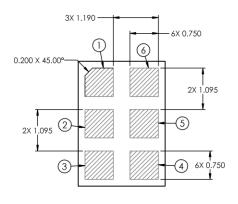




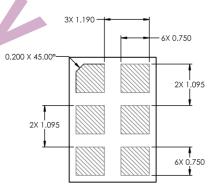
Item	Dimension	Tolerance
Length (L)	3.30	±0.10
Width (W)	2.30	±0.10
Height (H)	0.93	±0.10
PCB Thickness (T)	0.165	±0.05

Pin#	Pin Name	Туре	Description
1	Vdd	Power	Power Supply
2	CLOCK	Digital I	Clock Input
3, 4	GROUND	Power	Ground
5	SELECT	Digital I	Lo/Hi (L/R) Select
6	DATA	Digital O	PDM Output

## **Example Land Pattern**



## Example Solder Stencil Pattern



## NOTES



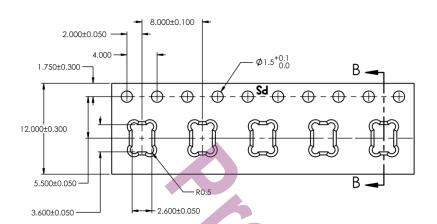
Pick Area only extends to 0.25 mm of any edge or hole unless otherwise specified. Dimensions are in millimeters unless otherwise specified.

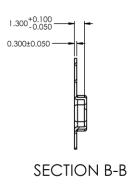
Tolerance is ±0.15mm unless otherwise specified





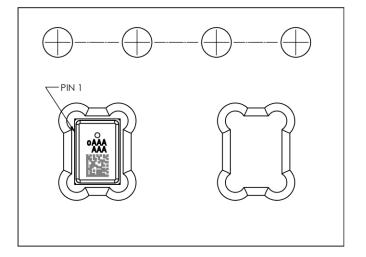
# PACKAGING & MARKING DETAIL





Model Number	Suffix	Reel Diameter	Quantity Pe Reel	er
V2S200D-1	-8	13"	5900	

Component	Surface Resistance (ohms)
Reel	10 <sup>5</sup> - 10 <sup>9</sup>
Carrier Tape	10 <sup>5</sup> - 10 <sup>9</sup>
Cover Tape	10 <sup>4</sup> - 10 <sup>10</sup>



Letter: "o", orientation mark (pin 1)

AAAAAA = Internal KN Code

2D barcode "ABCDEFGHJKLMNPQRSTUVWXYZ0123456789"

Unique Job Identification Number for product traceability

## NOTES

Dimensions are in millimeters unless otherwise specified.

Vacuum pickup only in the pick area indicated in Mechanical Specifications.

Tape & reel per EIA-481.

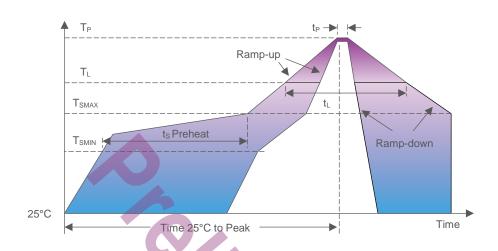
Labels applied directly to reel and external package.

Shelf life: Twelve (12) months when devices are stored in the factory-supplied, unopened ESD moisture sensitive bag under the maximum environmental conditions of 30°C, 70% R.H.





# RECOMMENDED REFLOW PROFILE



Profile Feature	Pb-Free
Average Ramp-up rate (T <sub>SMAX</sub> to T <sub>P</sub> )	3°C/second max.
Preheat  Temperature Min (T <sub>SMIN</sub> )  Temperature Max (T <sub>SMAX</sub> )  Time (T <sub>SMIN</sub> to T <sub>SMAX</sub> ) (t <sub>S</sub> )	150°C 200°C 60-180 seconds
Time maintained above:  Temperature (T <sub>L</sub> ) Time (t <sub>L</sub> )	217°C 60-150 seconds
Peak Temperature (T <sub>P</sub> )	260°C
Time within 5°C of actual Peak Temperature (t <sub>P</sub> )	20-40 seconds
Ramp-down rate (T <sub>P</sub> to T <sub>SMAX</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max

#### NOTES:

Based on IPC/JEDEC J-STD-020 Revision C.

All temperatures refer to topside of the package, measured on the package body surface.

The actual reflow profile used should be optimized based on the reflow requirements of all components, board design, solder paste formulation and reflow equipment used. Details of recommended handling and manufacturing processes can be found in AN25 SMT Manufacturing Guidelines for SiSonic™ Microphones.

## ADDITIONAL NOTES

- (A) Barometric relief hole must be open during reflow. No other special treatment is needed on the Barometric relief hole during assembly
- (B) MSL (moisture sensitivity level) Class 1.
- (C) Maximum of 3 reflow cycles is recommended.
- (D) In order to minimize device damage:
  - Do not board wash or clean after the reflow process.
  - Do not brush board with or without solvents after the reflow process.
  - Do not directly expose to ultrasonic processing, welding, or cleaning.
  - Do not apply a vacuum when repacking into sealed bags at a rate faster than 0.5 atm/sec.
  - Do not directly expose to vapor phase soldering.
  - Do not subject the sensor to strong mechanical agitation





# **MATERIALS STATEMENT**

Meets the requirements of the European RoHS directive 2011/65/EC as amended.

Meets the requirements of the industry standard IEC 61249-2-21:2003 for halogenated substances and Knowles Green Materials Standards Policy section on Halogen-Free.

Product is Beryllium Free according to limits specified on the Knowles Hazardous Material List (HSL for Products).

Ozone depleting substances are not used in the product or the processes used to make the product, including compounds listed in Annex A, B, and C of the "Montreal Protocol on Substances That Deplete the Ozone Layer.

## RELIABILITY SPECIFICATIONS

Test	Description
Thermal Shock	100 cycles of air-to-air thermal shock from -40C to +125C with 15 minute Soaks (IEC 68-2-14)
High Temperature	+105°C environment for 1,000 hours (JESD22-A103)
Low Temperature	-40°C environment for 1,000 hours (JESD22-A119)
ESD-HBM	3 discharges at ±2kV direct contact to I/O pins (ANSI/ESDA/JEDEC JS-001-2014)
ESD-HMM	10 discharges at ±8kV direct contact to lid when unit is grounded (AMSI/ESD SP5.6-2009)
ESD-CDM	3 discharges at ±500V (ANSI/ESDA/JEDEC JS-002-2014)
Reflow	5 reflow cycles with peak temperature of +260°C (JEDEC 22-A113F)
Mechanical Shock	3 pulses of 20,000g in each of the X, Y, Z directions (IEC 68-2-27 Test Ea)

## **NOTES**

Sensors meet all performance and electrical specifications before and after reliability testing, except sensitivity which can deviate up to 3dB.

After 3 reflow cycles, the sensitivity of the sensors shall not deviate more than 1 dB from its initial value.





# **SPECIFICATION REVISIONS**

Revision	Specification Changes	Date
1	Initial Preliminary Release	3/11/22
2	updated height, pcb thickness, frequency response,	10/13/22
3	Barometric relief hole comment Frequency response down to 100Hz THD vs GEE	11/14/22
4	Reliability comments Bandwidth update	11/30/22
5	Updated: Group delay, Phase, IDD vs VDD figures, Max supply voltage, Polarity description, Sound isolation condition, 1.2MHz Signal to Noise ratio, Low Power Mode sensitivity, Normal Mode sensitivity Removed: Fall-asleep time, Wake-up time	3/24/23

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